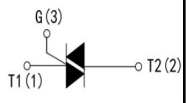
TRIAC series

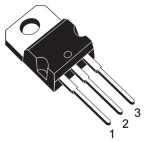
1 Description

T1635 series triacs with low holding and latchingcurrent are especially recommended for use onmiddle and small resistance type power load.

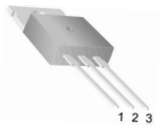
TO-220F series provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink.



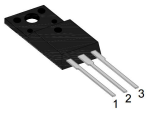
V_{RRM}/V_{DRM} =600/800V
V_{TM} =≤1.55V
$I_{T(RMS)}$ =16A



TO-220M



TO-220C



TO-220F-2L
Insulated

2 Features

- High current output up to 16A
- Low Peak on-state voltage drop
- High voltage
- High reliability

3 Applications

- jet pumps of dishwashers
- fans of air-conditioner
- power charger
- AC Motor control

4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25℃,unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (Tj=25℃)		V_{DRM}	600/800	V
Repetitive peak reverse voltage (Tj=25℃)		V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	+ 100	V
Non repetitive peak reverse voltage		V_{RSM}	+ 100	V
RMS on-state current	TO-220F(Ins) (TC=95℃)	$I_{T(RMS)}$	16	A
	TO-220(Non-Ins) (TC=105℃)			
Non repetitive surge peak on-state current	tp=8.3ms	I_{TSM}	170	A
	tp=10ms		160	
I^2t value for fusing (tp=10ms)		I^2t	144	A
Repetitive rate of rise of on-state current (ITM=20A IG=50mA dIG/dt 50mA/ms)		$d_{IT/dt}$	50	A/us
Peak gate current		I_{GM}	4	A
Peak gate power		P_{GM}	10	W
Average gate power dissipation		$P_{G(AV)}$	1	W
Operating junction temperature range		T_J	- 40 ~ 150	℃
Storage junction temperature range		T_{STG}	- 40 ~ 150	℃

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE			UNIT
		TO-220M	TO-220C	TO-220F	
Thermal Resistance, Junction to Case-sink	R_{thJC}	2.2	2.0	3.5	℃/W

4.3 Electrical Characteristics (Tc=25℃,unless otherwise noted)

SYMBOL	PARAMETER	Test Conditions		Min	Typ	Max	Unit
I_{GT}	Triggering gate current	V_D=12V R_L=33Ω	Ⅰ-Ⅱ-Ⅲ	-	-	35	mA
			Ⅳ	-	-	-	
V_{GT}	Triggering gate voltage		ALL	-	0.8	1.3	V
V_{GD}	Non-triggering gate voltage	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ		0.2	-	-	V
I_L	Latching Current	I_G=1.2I_{GT}	Ⅰ-Ⅲ	-	-	60	mA
			Ⅱ	-	-	70	
I_H	Holding Current	I_T=100mA		-	-	50	mA
dv/dt	Critical Rate of Rise of Off-state Voltage	V_D=2/3V_{DRM} Gate Open T_j=125℃		500	-	-	V/us
V_{TM}	Peak Forward On-State Voltage	I_{TM}=23A tp=380us		-	-	1.55	V
I_{DRM}	Maximum forward or reverse leakage current	V_D=V_{DRM} V_R=V_{RRM}	Tj=25℃	-	-	10	uA
I_{RRM}	Maximum reverse leakage current		Tj=125℃	-	-	500	uA

5 Typical characteristics diagrams

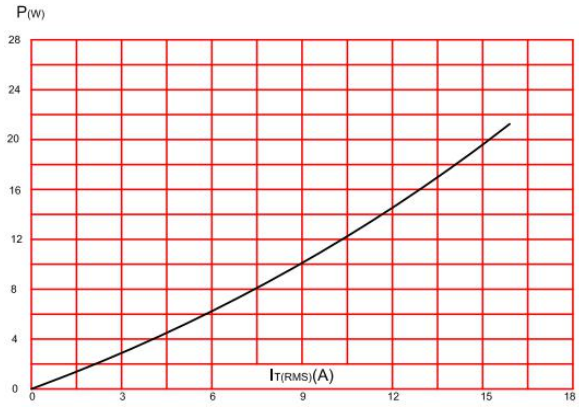


FIG.1: Maximum power dissipation versus RMS on-state current

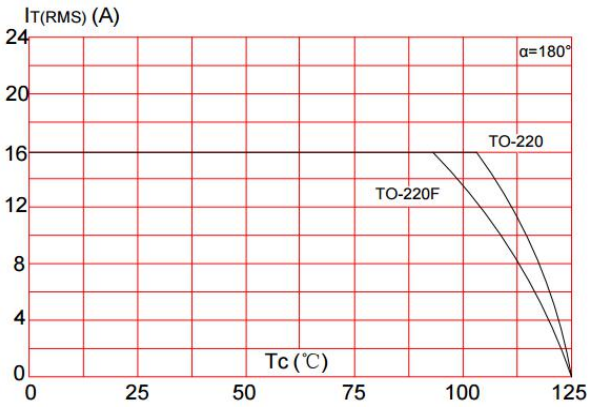


FIG.2: RMS on-state current versus case temperature

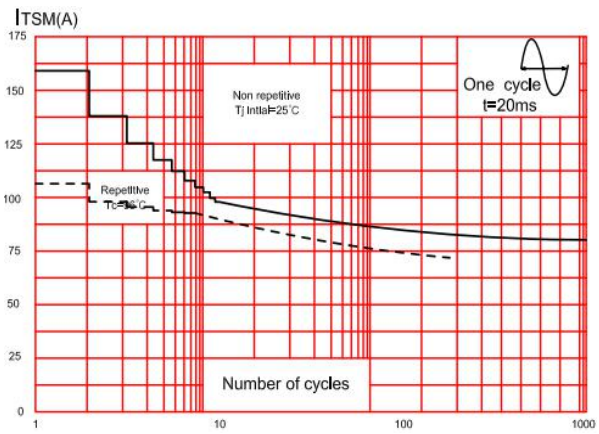


FIG.3: Surge peak on-state current versus number of cycles

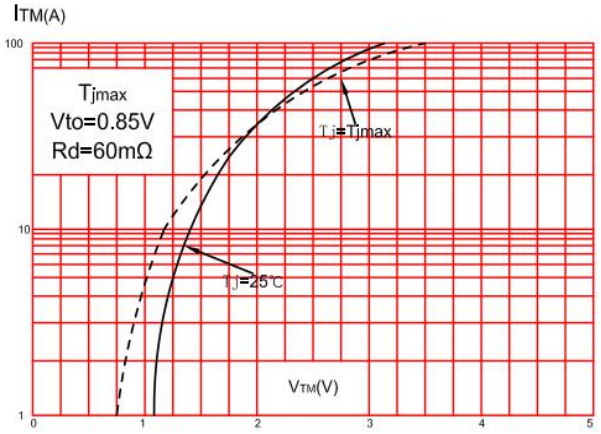


FIG.4: On-state characteristics (maximum values)

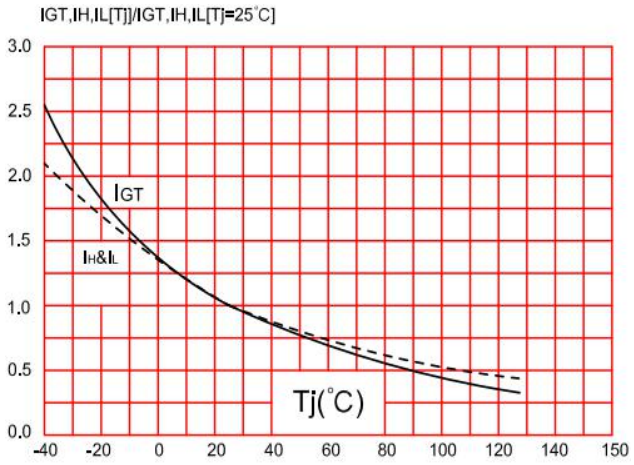
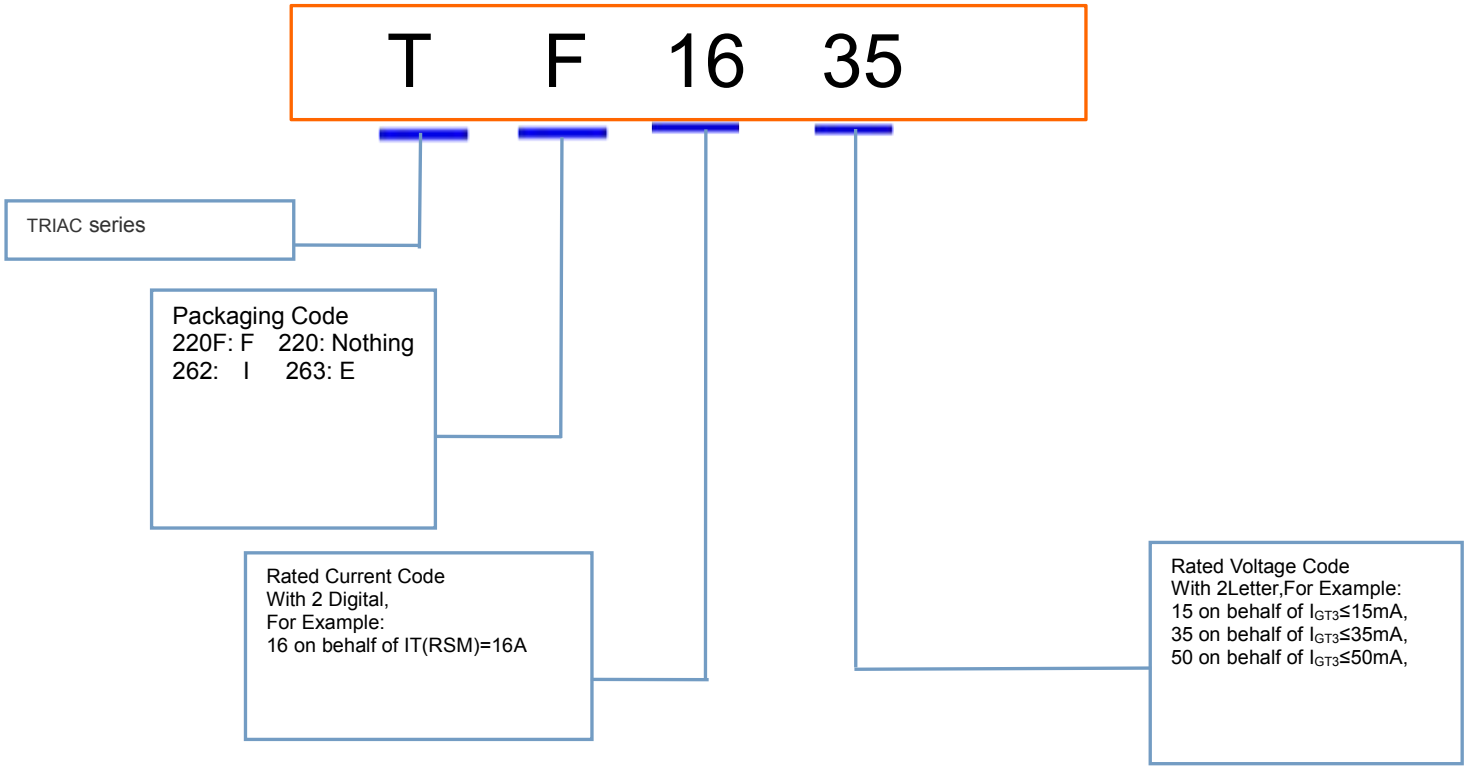


FIG.5: Relative variations of gate trigger current, holding current and latching current versus junction temperature

6 Product Names Rules

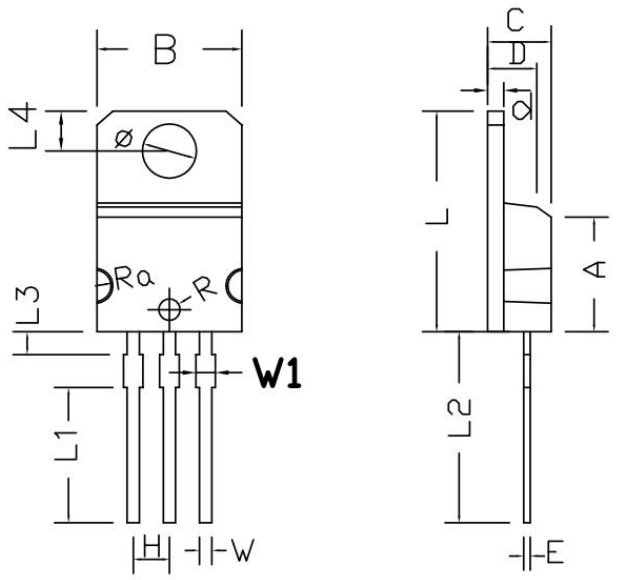


7 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
T1635	TO-220M	T1635	Pb-free	Tube	1000//box
T1635	TO-220C	T1635	Pb-free	Tube	1000//box
TF1635	TO-220F	TF1635	Pb-free	Tube	1000//box

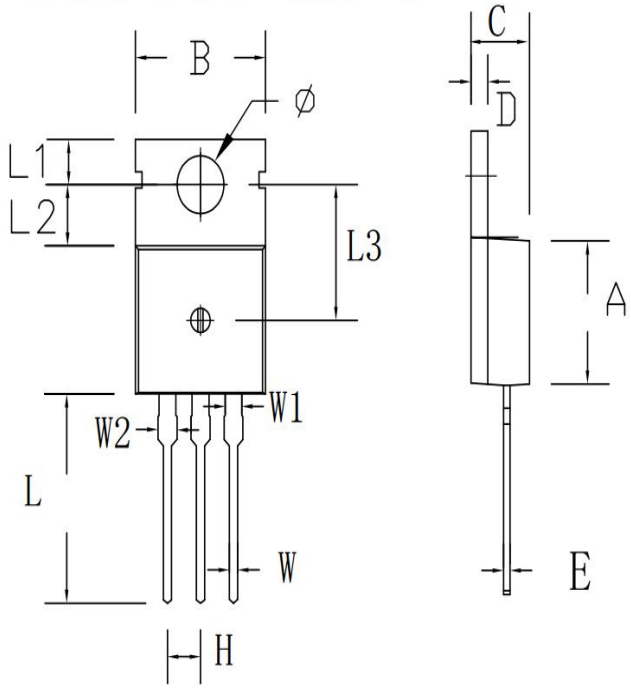
8 Dimensions

TO-220M PACKAGE OUTLINE DIMENSIONS



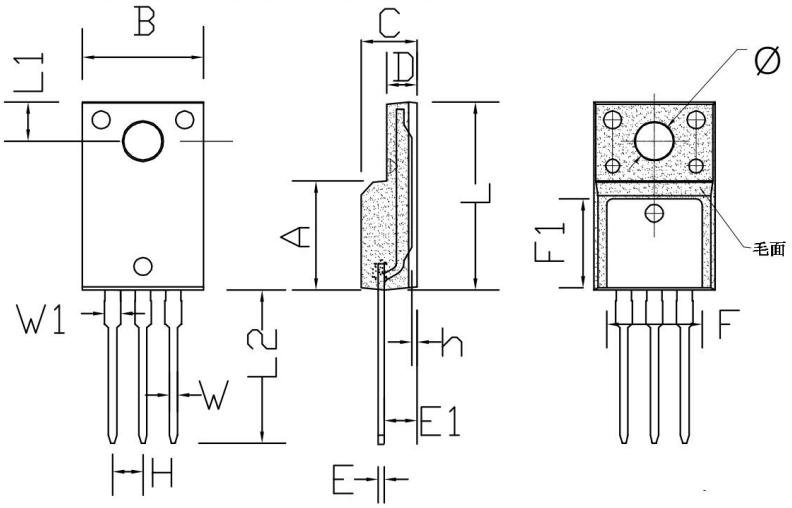
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
	MIN	MAX	MIN	MAX
A	8.03	8.05	0.316	0.317
B	10.13	10.23	0.399	0.403
C	4.42	4.52	0.174	0.178
D	3.42	3.52	0.135	0.139
E	0.44	0.46	0.017	0.018
L	15.25	15.45	0.601	0.609
H	2.52	2.56	0.099	0.101
W	0.85	0.87	0.033	0.034
Φ	3.78	3.82	0.149	0.151
R	0.74	0.76	0.029	0.030
Ra	9.44	9.48	0.372	0.374
d	1.28	1.32	0.050	0.052
L1	9.4	9.6	0.370	0.378
L2	13.22	13.62	0.521	0.537
L3	1.52	1.72	0.060	0.068
L4	2.7	2.9	0.106	0.114
W1	1.32	1.42	0.052	0.056

TO-220C PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
H	2.54 TYP		0.100 TYP	
W	0.60	0.95	0.024	0.037
W1	1.05	1.45	0.041	0.057
W2	1.20	1.60	0.047	0.063
L	12.60	13.40	0.496	0.528
L1	2.45	2.95	0.096	0.116
L2	3.45	3.95	0.136	0.156
L3	8.15	8.65	0.321	0.341
Φ	3.50	3.90	0.138	0.154

TO-220F PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	10.00	10.50	0.394	0.413
C	4.30	4.90	0.169	0.193
D	2.30	2.70	0.091	0.106
L	15.55	16.15	0.612	0.636
h	0.40	0.60	0.016	0.024
L1	3.15	3.55	0.124	0.140
L2	12.65	13.35	0.498	0.526
W	0.70	0.90	0.028	0.035
W1	1.15	1.55	0.045	0.061
H	2.54 TYP		0.100 TYP	
E	0.48	0.53	0.019	0.021
ϕ	2.90	3.40	0.114	0.134
E1	2.40	2.90	0.094	0.114
F	7.75	8.25	0.305	0.325
F1	7.35	7.85	0.289	0.309

9 Attentions

- ROUM Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Roma products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2017.08.14	1.0	Original	